

HiPerFRED

### **VBE60-12A**

$V_{RRM}$	=	1200 V
I <sub>dav</sub>	=	60 A
t <sub>rr</sub>	=	60 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery 1~ Rectifier Bridge

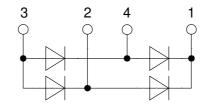
Part number

VBE60-12A



Backside: isolated





#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces: - Power dissipation within the diode
- Turn-on loss in the commutating switch

#### **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

#### Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolatedAdvanced power cycling

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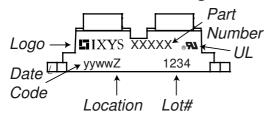
Fast Diode					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V <sub>RSM</sub>	max. non-repetitive reverse block	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{vJ} = 25^{\circ}C$			1200	V	
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> = 1200 V	$T_{VJ} = 25^{\circ}C$			250	μA	
		$V_{R} = 1200 V$	$T_{vJ} = 125^{\circ}C$			1	mA	
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 30 A	$T_{vJ} = 25^{\circ}C$			2.68	V	
		$I_{F} = 60 \text{ A}$				3.15	V	
		$I_{F} = 30 \text{ A}$	T <sub>vJ</sub> = 150°C			1.73	V	
		$I_{F} = 60 \text{ A}$				2.22	V	
I DAV	bridge output current	$T_c = 70^{\circ}C$	T <sub>vJ</sub> = 150°C			60	Α	
		rectangular d = 0.5						
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			1.31	V	
r <sub>F</sub>	slope resistance } for power lo	oss calculation only				14	mΩ	
<b>R</b> <sub>thJC</sub>	thermal resistance junction to cas	e				1.15	K/W	
R <sub>thCH</sub>	thermal resistance case to heatsir	nk			0.1		K/W	
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			110	W	
	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_{R} = 0 \text{ V}$	$T_{vJ} = 45^{\circ}C$			200	Α	
C	junction capacitance	$V_{R} = 600 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		12		pF	
I <sub>RM</sub>	max. reverse recovery current	N	$T_{vJ} = 25 °C$		8.5		А	
		$I_{\rm F} = 30  \text{A};  V_{\rm R} = 600  \text{V}$	$T_{vJ} = 100 ^{\circ}C$		13		Α	
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 30 A; V <sub>R</sub> = 600 V -di <sub>F</sub> /dt = 200 A/μs	$T_{VJ} = 25 °C$		60		ns	
		)	$T_{vJ} = 100 ^{\circ}C$		170		ns	

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Package	Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					150	Α
$\mathbf{T}_{v_J}$	virtual junction temperature				-40		150	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature						150	°C
Weight						30		g
M <sub>D</sub>	mounting torque						1.5	Nm
M <sub>T</sub>	terminal torque						1.5	Nm
d <sub>Spp/App</sub>	oroonago distanco on curfa	terminal to terminal	10.5	3.2			mm	
<b>d</b> <sub>Spb/Apb</sub>	creepage distance on suna	page distance on surface   striking distance through air		8.6	6.8			mm
V	isolation voltage	t = 1 second			3000			۷
	t = 1 minute		50/60 Hz, RMS; lıso∟ ≤ 1 mA		2500			V

**Product Marking** 



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VBE60-12A	VBE60-12A	Tube	10	514294

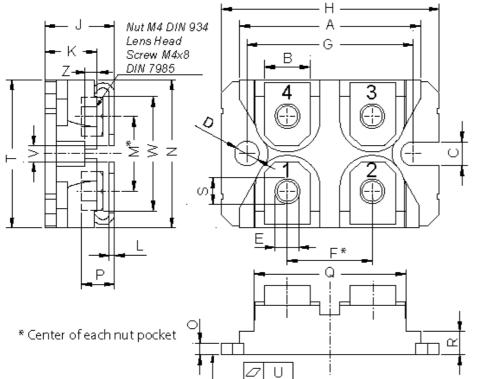
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}C$
	)[_ <b>R</b> ₀_]-	Fast Diode		
V <sub>0 max</sub>	threshold voltage	1.31		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	12		mΩ

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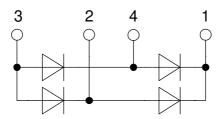
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#### Outlines SOT-227B (minibloc)



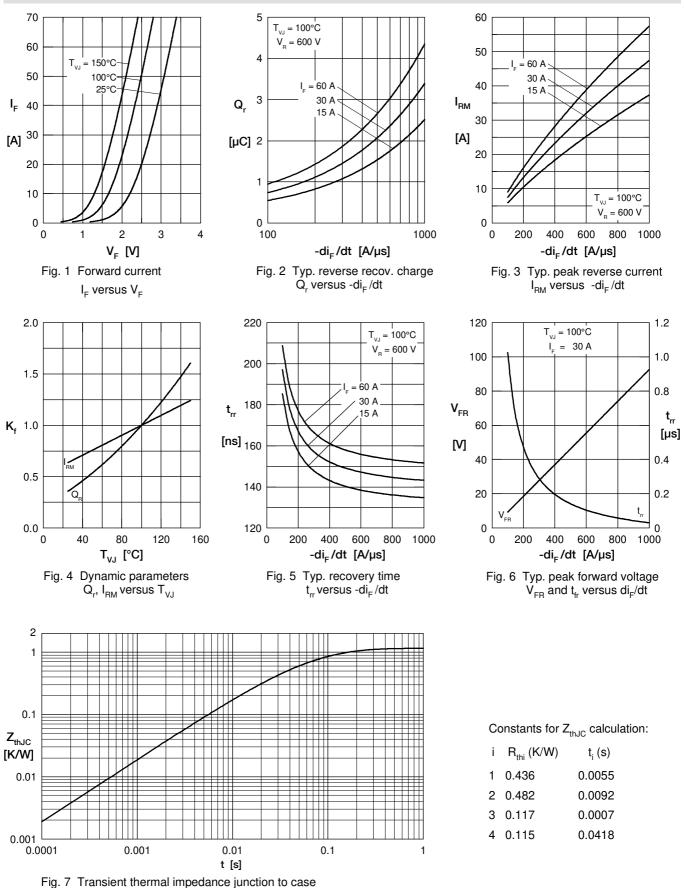
Dim.	Millir	neter	Inches		
Dim.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
B	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
К	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
Μ	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Ρ	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	





## **VBE60-12A**







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25.330.1653.1	25.330.4753.1	25.330.5253.1	25.334.3253.1	25.334.3353.1	25.350.2053.0	25.352.4753.1	25.522.3253.0	<u>T483C</u> <u>T484C</u>
<u>T485F</u> <u>T485H</u>	T512F-YEB	<u>T513F</u> <u>T514F</u>	T554 T612FSE	25.161.3453.0	25.179.2253.0	25.194.3253.0	25.325.1253.1	25.326.4253.1
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25.602.4053.0								